NSN 5962-01-416-0409

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-416-0409 **Body Length:** 2.540 inches **Body Width:** 2.540 inches **Body Height:** 0.103 inches **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** F-16 **Features Provided:** Bipolar and burn in, mil-std-883, class b and electrostatic sensitive and hermetically sealed and programmed and tested to mil-std-883 **Inclosure Material:** Ceramic **Inclosure Configuration:** Leaded chip carrier **Output Logic Form:** Bipolar metal-oxide semiconductor **Criticality Code Justification:** Cbbl **Terminal Surface Treatment:** Solder **Product Name:** Microcircuit, asic, digital, symbol generator **Voltage Rating And Type Per Characteristic:** -0.5 volts input and 5.0 volts input and -0.5 volts power source and 6.0 volts power source **Memory Device Type:** Pal **Special Features:** 112, 000 gate count; ti tbg1000 0.8 micron bi-cmos technology; four functions-bus interface, symbol generator, symbol occlusion and symbol scan conversion functions; max clock frequency is 40 mhz **Test Data Document:** 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). **Terminal Type And Quantity:** 196 beam lead Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

NSN 5962-01-416-0409

Memory Microcircuit - Page 2 of 2



Fiig:

A458a0